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Should be replaced with:

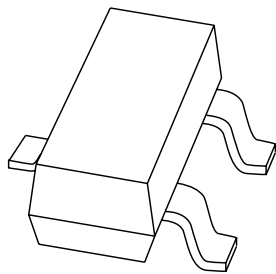
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Kind regards,

Team Nexperia

# DATA SHEET



## **BC849; BC850** NPN general purpose transistors

Product data sheet  
Supersedes data of 1999 Apr 08

2004 Jan 16

# NPN general purpose transistors

# BC849; BC850

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

NPN transistor in a SOT23 plastic package.  
 PNP complements: BC859 and BC860.

### MARKING

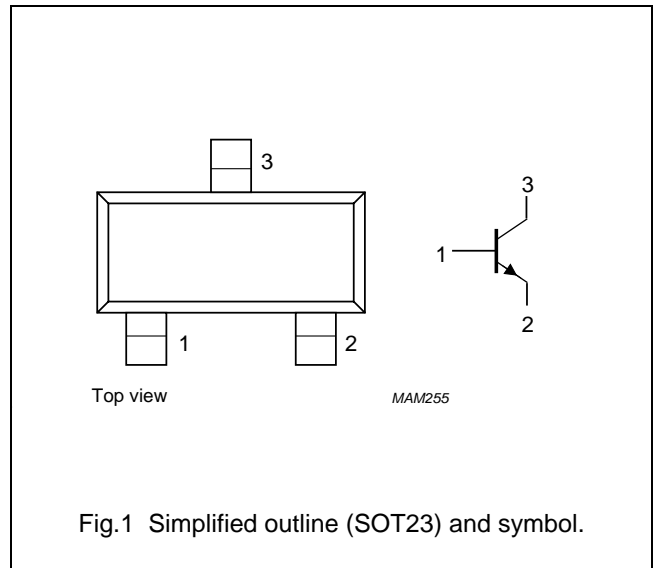
TYPE NUMBER	MARKING CODE <sup>(1)</sup>	TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BC849B	2B*	BC850B	2F*
BC849C	2C*	BC850C	2G*

### Note

- \* = p : Made in Hong Kong.  
 \* = t : Made in Malaysia.  
 \* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC849B	-	plastic surface mounted package; 3 leads	SOT23
BC849C			
BC850B			
BC850C			

## NPN general purpose transistors

## BC849; BC850

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	30	V
	BC849				
V <sub>CEO</sub>	collector-emitter voltage	open base	–	30	V
	BC850				
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
I <sub>BM</sub>	peak base current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## NPN general purpose transistors

## BC849; BC850

**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

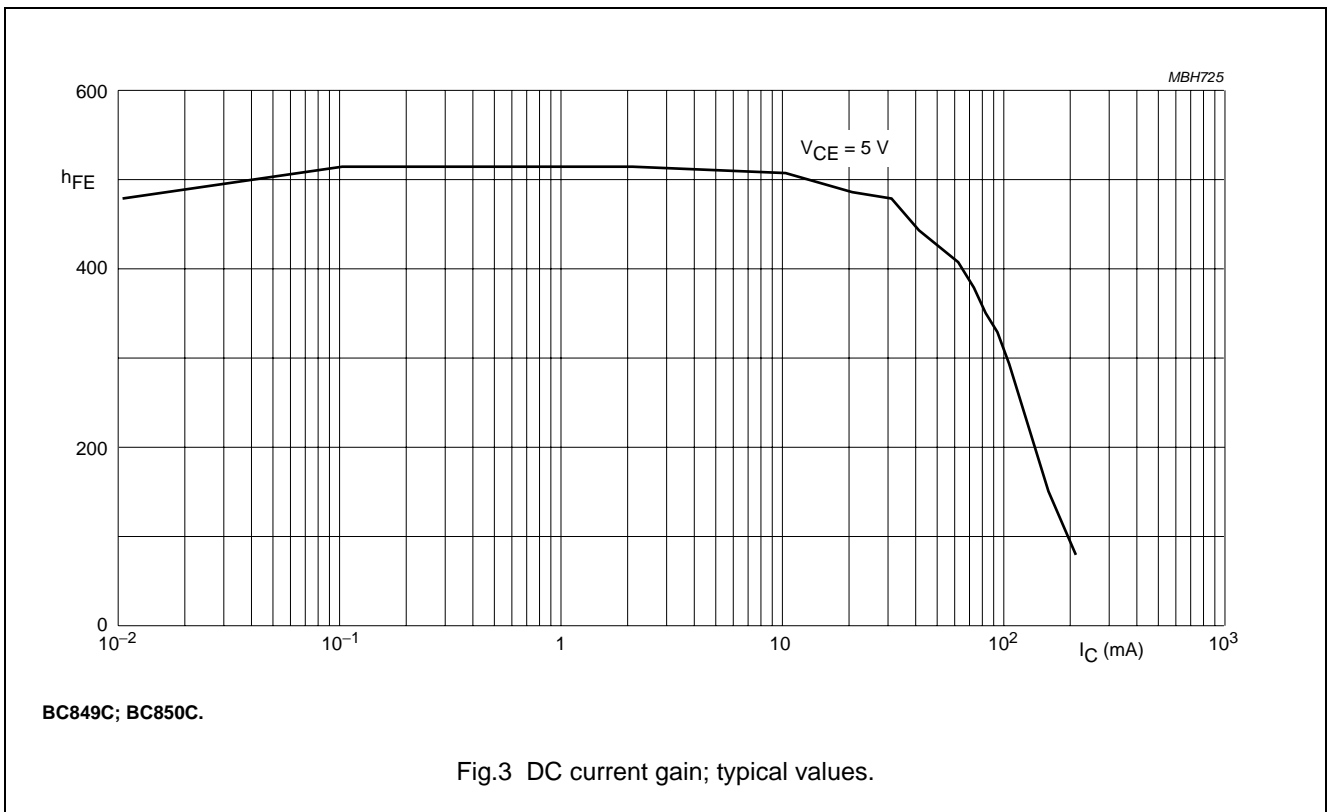
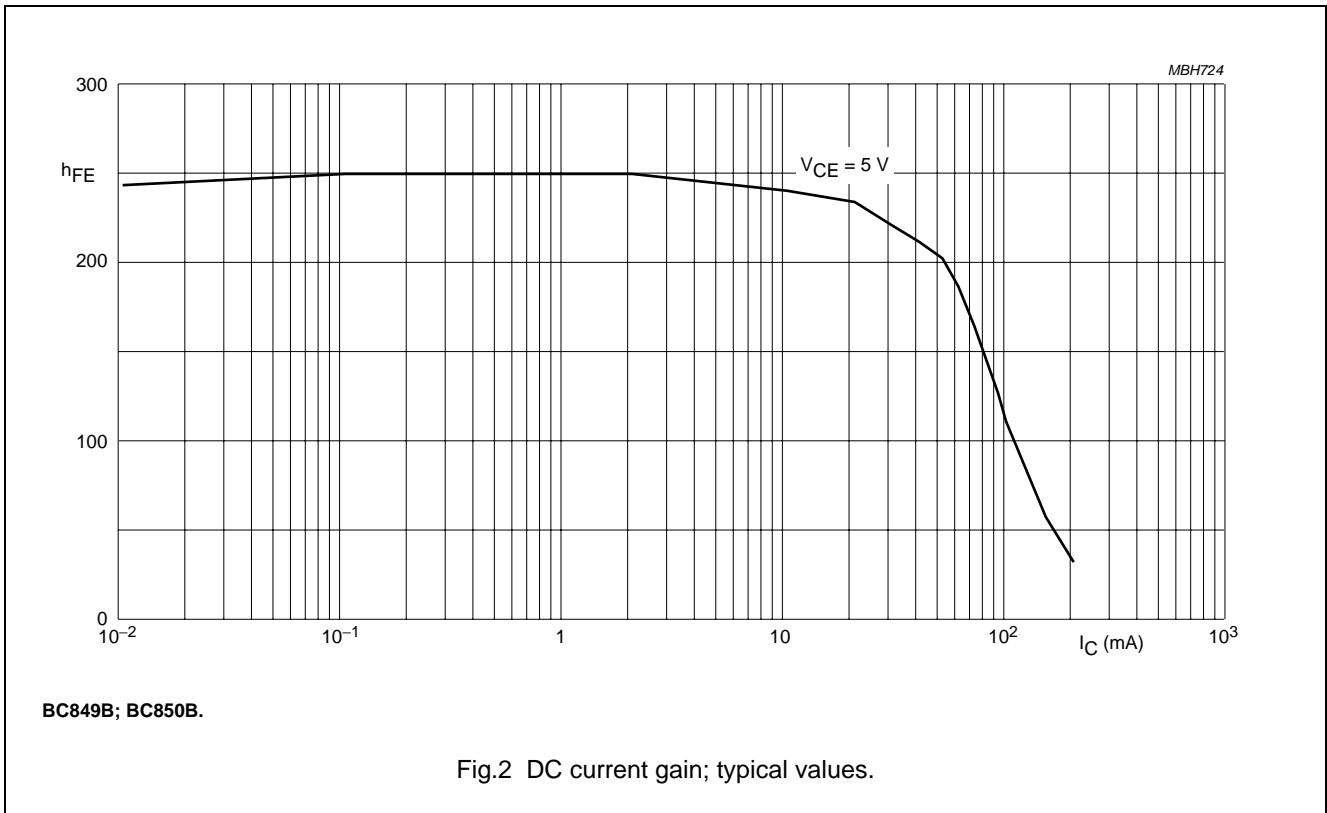
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain BC849B; BC850B	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ see Figs 2 and 3	–	240	–	
	BC849C; BC850C		–	450	–	
$h_{FE}$	DC current gain BC849B; BC850B	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ see Figs 2 and 3	200	290	450	
	BC849C; BC850C		420	520	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA};$ note 1	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA};$ note 1	–	900	–	mV
$V_{BE}$	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ note 2	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V};$ note 2	–	–	770	mV
$C_c$	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
$C_e$	emitter capacitance	$I_C = I_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	11	–	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
		$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

**Notes**

- $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.
- $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

NPN general purpose transistors

BC849; BC850



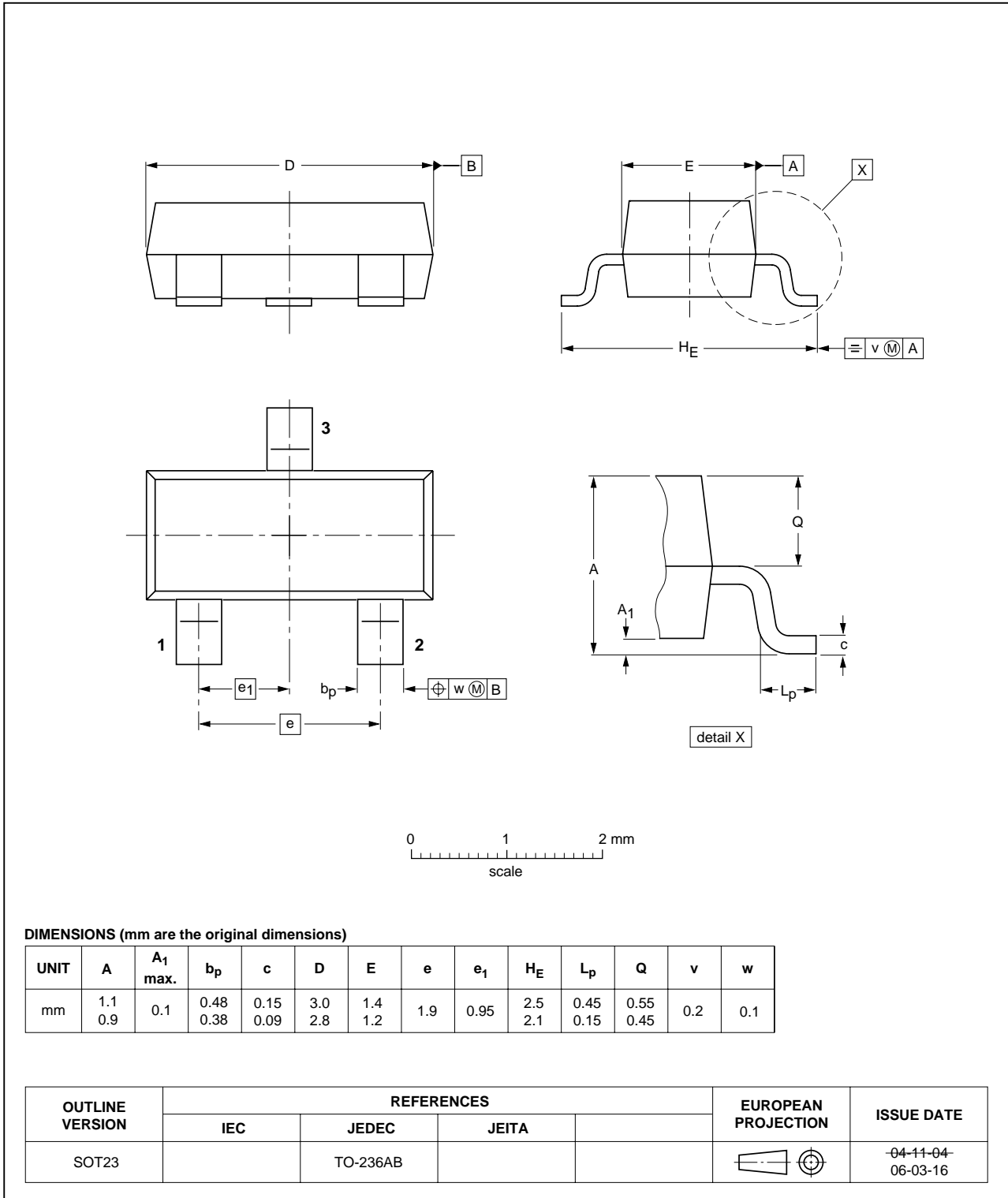
NPN general purpose transistors

BC849; BC850

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



## NPN general purpose transistors

BC849; BC850

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

## Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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